Scanning tunneling microscopy/spectroscopy study of graphene – MoS$_2$ heterojunction$^1$ SHIVANI RAJPUT, YAOYI LI, DUSHYANT TOMER, LIAN LI, University of Wisconsin, Milwaukee — Atomic scale topographic fluctuations are relevant to a number of graphene applications including graphene / semiconductor Schottky diodes [1,2]. In this work, we investigate the atomic structures and electronic properties of graphene-MoS$_2$ heterojunction fabricated by transferring chemical vapor deposited monolayer graphene onto mechanically exfoliated multilayer MoS$_2$. Scanning tunneling microscopy reveals the formation of Moiré patterns with corrugations $\sim 0.03$ nm, but no ripples, in contrast to graphene-SiC junctions [1,2]. Scanning tunneling spectroscopy further indicates that the periodic modulations of the Moiré pattern do not influence the electronic properties of the junction. Additional states near the Fermi level are also observed, likely due to impurities trapped at the interface during graphene transfer. These results and their impact on the properties of the van der Waals graphene-MoS$_2$ heterojunction will be discussed at the meeting.


$^1$Supported by U.S. Department of Energy, Office of Basic Energy Sciences, Division of Materials Sciences and Engineering under Award DE-FG02-07ER46228.

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Date submitted: 14 Nov 2014

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